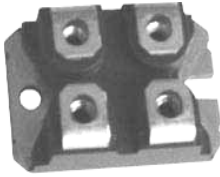
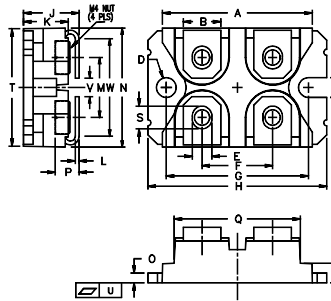


SMOS44/48N50D2, SMOS44/48N50D3

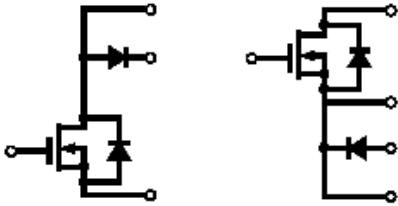
Power MOSFETs



Dimensions SOT-227(ISOTOP)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033



	Symbol	Test Conditions	Maximum Ratings	Unit	
HIPerFET MOSFET	V _{DSS}	T _J =25°C to 150°C	500	V	
	V _{DGR}	T _J =25°C to 150°C; R _{GS} =1MΩ	500		
	V _{GS}	Continuous	±20	V	
	V _{GSM}	Transient	±30		
	I _{D25}	T _C =25°C	44N50	44	A
			48N50	48	
	I _{DM}	T _C =25°C; pulse width limited by max. T _{JM}	44N50	176	A
			48N50	192	
	I _{AR}	T _C =25°C	24	A	
E _{AR}	Repetitive	30	mJ		
dv/dt	I _S ≤ I _{DM} ; -di/dt ≤ 100A/us; V _{DD} ≤ V _{DSS} T _J ≤ 150°C; R _G =2Ω	5	V/ns		
P _D	T _C =25°C	520	W		
DIODE	V _{RRM}		600	V	
	I _{FAVM}	T _C =70°C; rectangular; d=0.5	60	A	
	I _{FRM}	t _p < 10us; pulse width limited by T _J	800	A	
	P _D	T _C =25°C	180	W	
CASE	T _J		-40...+150	°C	
	T _{JM}		150		
	T _{stg}		-40...+150		
	V _{ISOL}	50/60 Hz, RMS t=1 min I _{ISOL} ≤ 1 mA t=1 s	2500	V~	
			3000		
M _d	Mounting torque	1.5/13	Nm/lb.in.		
	Terminal connection torque(M4)	1.5/13			
Weight		30	g		

